

SCHOTTKY BARRIER RECTIFIER

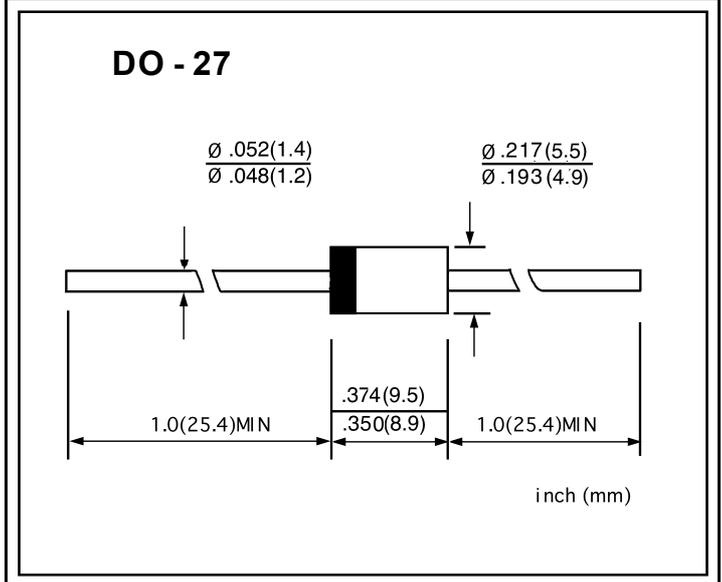
VOLTAGE RANGE: 20 --- 100 V
CURRENT: 3.0 A

FEATURES

- ◇ Metal-Semiconductor junction with guard ring
- ◇ Epitaxial construction
- ◇ Low forward voltage drop, low switching losses
- ◇ High surge capability
- ◇ For use in low voltage, high frequency inverters free wheeling, and polarity protection applications
- ◇ The plastic material carries U/L recognition 94V-0

MECHANICAL DATA

- ◇ Case: JEDEC DO--27, molded plastic
- ◇ Terminals: Axial lead, solderable per MIL-STD-750, Method 2026
- ◇ Polarity: Color band denotes cathode
- ◇ Weight: 0.041 ounces, 1.15 grams
- ◇ Mounting position: Any



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate by 20%.

		SB320	SB330	SB340	SB350	SB360	SB380	SB3A0	UNITS
Maximum recurrent peak reverse voltage	V_{RRM}	20	30	40	50	60	80	100	V
Maximum RMS voltage	V_{RMS}	14	21	28	35	42	56	70	V
Maximum DC blocking voltage	V_{DC}	20	30	40	50	60	80	100	V
Maximum average forward rectified current 9.5mm lead length, @ $T_A=75^\circ C$	$I_{F(AV)}$	3.0							A
Peak forward surge current 8.3ms single half-sine-wave superimposed on rated load @ $T_J=125^\circ C$	I_{FSM}	80.0							A
Maximum instantaneous forward voltage @ 3.0A (Note 1)	V_F	0.55		0.7		0.85		V	
Maximum reverse current @ $T_A=25^\circ C$ at rated DC blocking voltage @ $T_A=100^\circ C$	I_R	20.0			10.0				mA
Typical junction capacitance (Note2)	C_J	250			160				pF
Typical thermal resistance (Note3)	R_{JA}	40							°C
Operating junction temperature range	T_J	- 55 ---- + 125			- 55 ---- + 150				°C
Storage temperature range	T_{STG}	- 55 ---- + 150							°C

NOTE: 1. Pulse test: 300us pulse width, 1% duty cycle.

2. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.

3. Thermal resistance junction to ambient

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FIG.1 -- FORWARD CURRENT DERATING CURVE

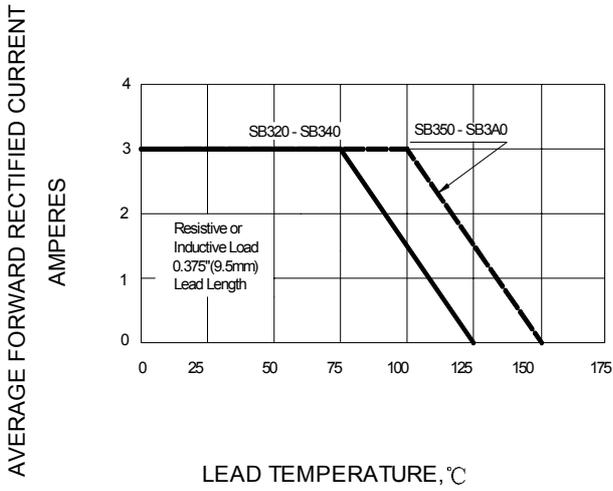


FIG.2 -- PEAK FORWARD SURGE CURRENT

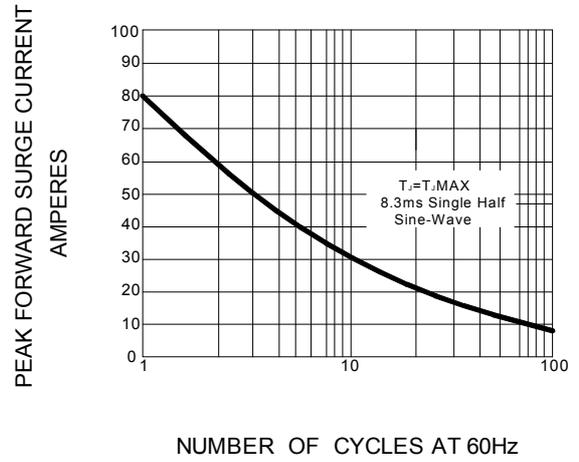


FIG.3 -- TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

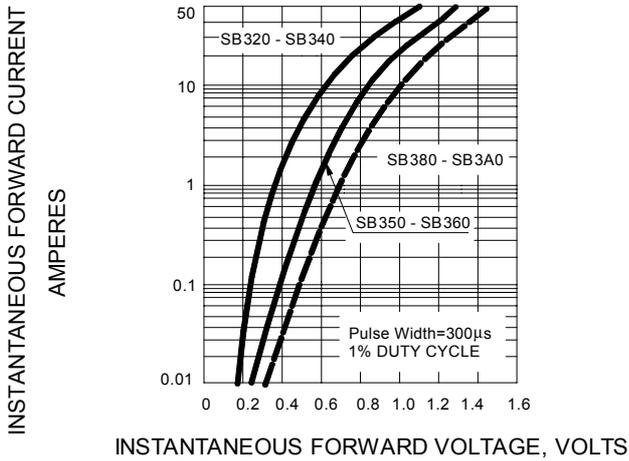


FIG.4 -- TYPICAL JUNCTION CAPACITANCE

